

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

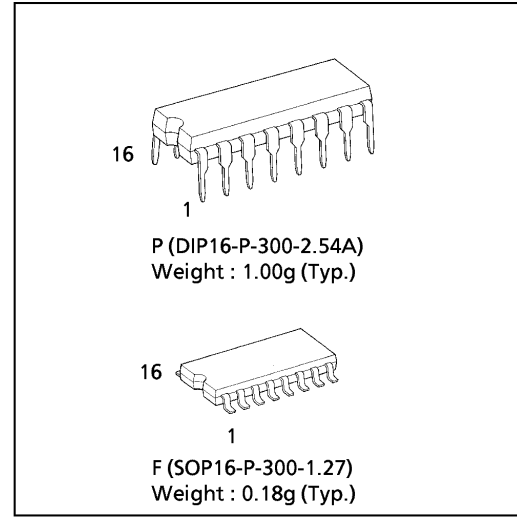
TC74HC279AP, TC74HC279AF

QUAD \bar{S} - \bar{R} LATCH

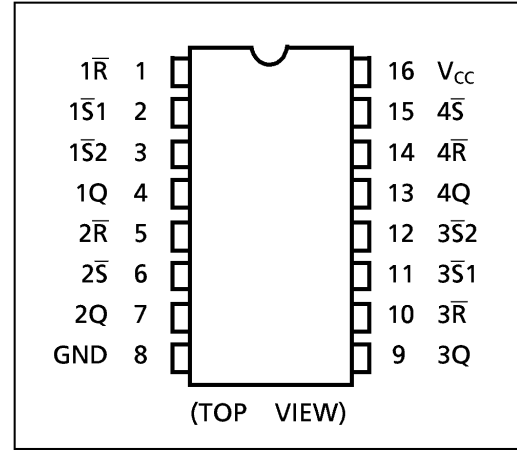
The TC74HC279A is a high speed CMOS QUAD S - R LATCH fabricated with silicon gate C²MOS technology. It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation. Each latch has an independent Q output and Set and Reset inputs. \bar{S} and \bar{R} are active low. When \bar{S} input is low, the Q output goes high and when \bar{R} input is low, the Q output goes low. When both \bar{S} and \bar{R} are low, \bar{S} takes precedence resulting Q=low. When both of \bar{S} and \bar{R} are held high, Q output doesn't change. All inputs are equipped with protection circuits against static discharge or transient excess voltage.

FEATURES :

- High Speed..... $t_{pd} = 12ns(typ.)$ at $V_{CC} = 5V$
- Low Power Dissipation..... $I_{CC} = 2\mu A(Max.)$ at $T_a = 25^\circ C$
- High Noise Immunity..... $V_{NIH} = V_{NIL} = 28\% V_{CC} (Min.)$
- Symmetrical Output Impedance... $|I_{OH}| = I_{OL} = 4mA(Min.)$
- Balanced Propagation Delays..... $t_{pLH} \approx t_{pHL}$
- Wide Operating Voltage Range... $V_{CC} (opr.) = 2V \sim 6V$
- Pin and Function Compatible with 74LS279



PIN ASSIGNMENT

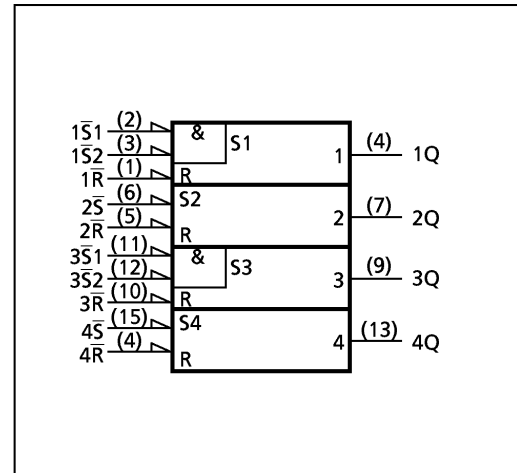


TRUTH TABLE

INPUTS		OUTPUTS
S #	\bar{R}	Q
H	H	Qn
L	H	H
H	L	L
L	L	H

NOTE :
 Qn -- The level of Q before the indicated input condition were established.
 # -- For latches with doubles \bar{S} input.
 H = Both \bar{S} input high
 L = One of both inputs low

IEC LOGIC SYMBOL



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ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V_{CC}	-0.5~7	V
DC Input Voltage	V_{IN}	-0.5~ $V_{CC} + 0.5$	V
DC Output Voltage	V_{OUT}	-0.5~ $V_{CC} + 0.5$	V
Input Diode Current	I_{IK}	± 20	mA
Output Diode Current	I_{OK}	± 20	mA
DC Output Current	I_{OUT}	± 25	mA
DC V_{CC} / Ground Current	I_{CC}	± 50	mA
Power Dissipation	P_D	500 (DIP)* / 180 (SOP)	mW
Storage Temperature	T_{stg}	-65~150	°C

*500mW in the range of $T_a = -40^{\circ}\text{C} \sim 65^{\circ}\text{C}$. From $T_a = 65^{\circ}\text{C}$ to 85°C a derating factor of $-10\text{mW}/^{\circ}\text{C}$ shall be applied until 300mW.

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V_{CC}	2~6	V
Input Voltage	V_{IN}	0~ V_{CC}	V
Output Voltage	V_{OUT}	0~ V_{CC}	V
Operating Temperature	T_{opr}	-40~85	°C
Input Rise and Fall Time	t_r, t_f	0~1000 ($V_{CC} = 2.0\text{V}$) 0~500 ($V_{CC} = 4.5\text{V}$) 0~400 ($V_{CC} = 6.0\text{V}$)	ns

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	$T_a = 25^{\circ}\text{C}$			$T_a = -40 \sim 85^{\circ}\text{C}$		UNIT	
				MIN.	TYP.	MAX.	MIN.	MAX.		
High - Level Input Voltage	V_{IH}		2.0	1.50	—	—	1.50	—	V	
			4.5	3.15	—	—	3.15	—		
			6.0	4.20	—	—	4.20	—		
Low - Level Input Voltage	V_{IL}		2.0	—	—	0.50	—	0.50	V	
			4.5	—	—	1.35	—	1.35		
			6.0	—	—	1.80	—	1.80		
High - Level Output Voltage	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -20\mu\text{A}$	2.0	1.9	2.0	—	1.9	—	V
				4.5	4.4	4.5	—	4.4	—	
			$I_{OH} = -4\text{mA}$ $I_{OH} = -5.2\text{mA}$	4.5	4.18	4.31	—	4.13	—	
				6.0	5.68	5.80	—	5.63	—	
Low - Level Output Voltage	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 20\mu\text{A}$	2.0	—	0.0	0.1	—	0.1	V
				4.5	—	0.0	0.1	—	0.1	
			$I_{OL} = 4\text{mA}$ $I_{OL} = 5.2\text{mA}$	4.5	—	0.17	0.26	—	0.33	
				6.0	—	0.18	0.26	—	0.33	
Input Leakage Current	I_{IN}	$V_{IN} = V_{CC}$ or GND	6.0	—	—	± 0.1	—	± 1.0	μA	
Quiescent Supply Current	I_{CC}	$V_{IN} = V_{CC}$ or GND	6.0	—	—	2.0	—	20.0		

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AC ELECTRICAL CHARACTERISTICS ($C_L = 15\text{pF}$, $V_{CC} = 5\text{V}$, $T_a = 25^\circ\text{C}$, Input $t_r = t_f = 6\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Output Transition Time	t_{TLH} t_{THL}		—	4	8	ns
Propagation Delay Time ($\bar{S}1, \bar{S}2 - Q$)	t_{pLH} t_{pHL}		—	12	22	
Propagation Delay Time ($\bar{S} - Q$)	t_{pLH} t_{pHL}		—	9	17	
Propagation Delay Time ($\bar{R} - Q$)	t_{pLH} t_{pHL}		—	11	20	

AC ELECTRICAL CHARACTERISTICS ($C_L = 50\text{pF}$, Input $t_r = t_f = 6\text{ns}$)

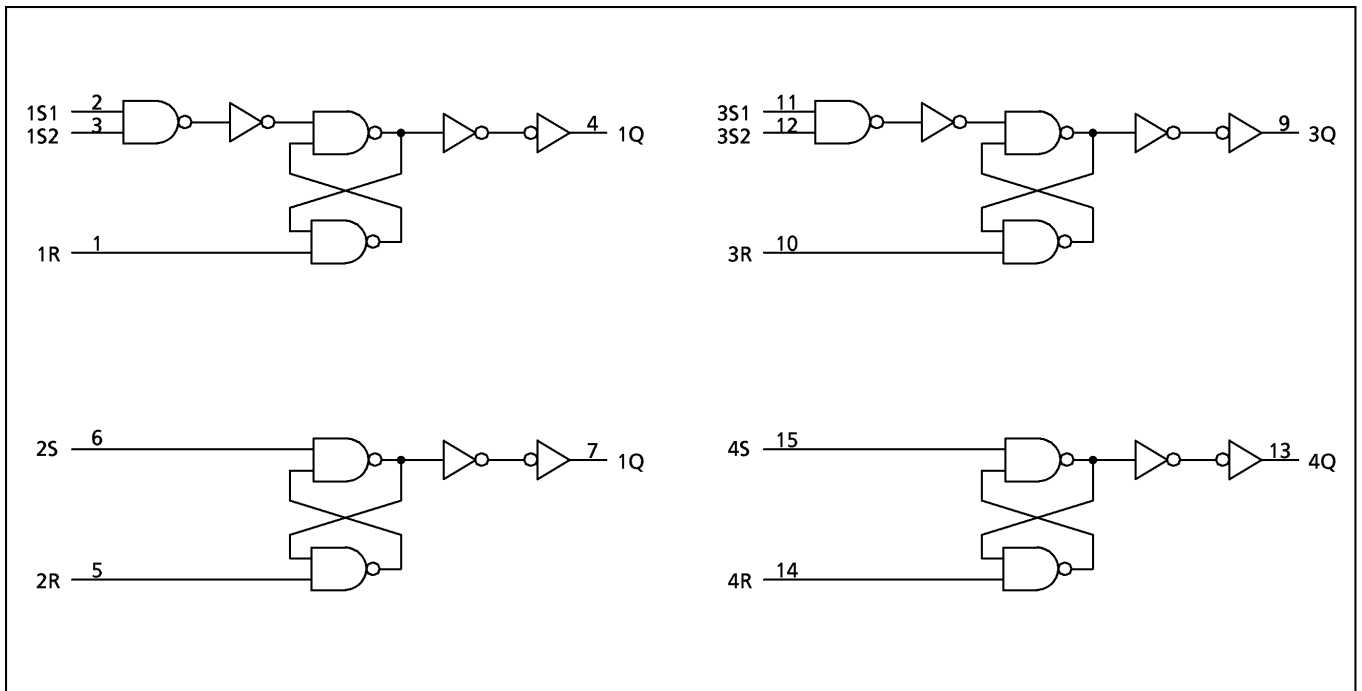
PARAMETER	SYMBOL	TEST CONDITION	$T_a = 25^\circ\text{C}$			$T_a = -40 \sim 85^\circ\text{C}$		UNIT
			$V_{CC}(\text{V})$	MIN.	TYP.	MAX.	MIN.	
Output Transition Time	t_{TLH} t_{THL}		2.0	—	30	75	—	95
			4.5	—	8	15	—	19
			6.0	—	7	13	—	16
Propagation Delay Time ($\bar{S}1, \bar{S}2 - Q$)	t_{pLH} t_{pHL}		2.0	—	45	130	—	165
			4.5	—	15	26	—	33
			6.0	—	13	22	—	28
Propagation Delay Time ($\bar{S} - Q$)	t_{pLH} t_{pHL}		2.0	—	38	100	—	125
			4.5	—	12	20	—	25
			6.0	—	10	17	—	21
Propagation Delay Time ($\bar{R} - Q$)	t_{pLH} t_{pHL}		2.0	—	42	120	—	150
			4.5	—	14	24	—	30
			6.0	—	12	20	—	26
Input Capacitance	C_{IN}		—	5	10	—	10	pF
Power Dissipation Capacitance	$C_{PD}(1)$		—	18	—	—	—	

Note (1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

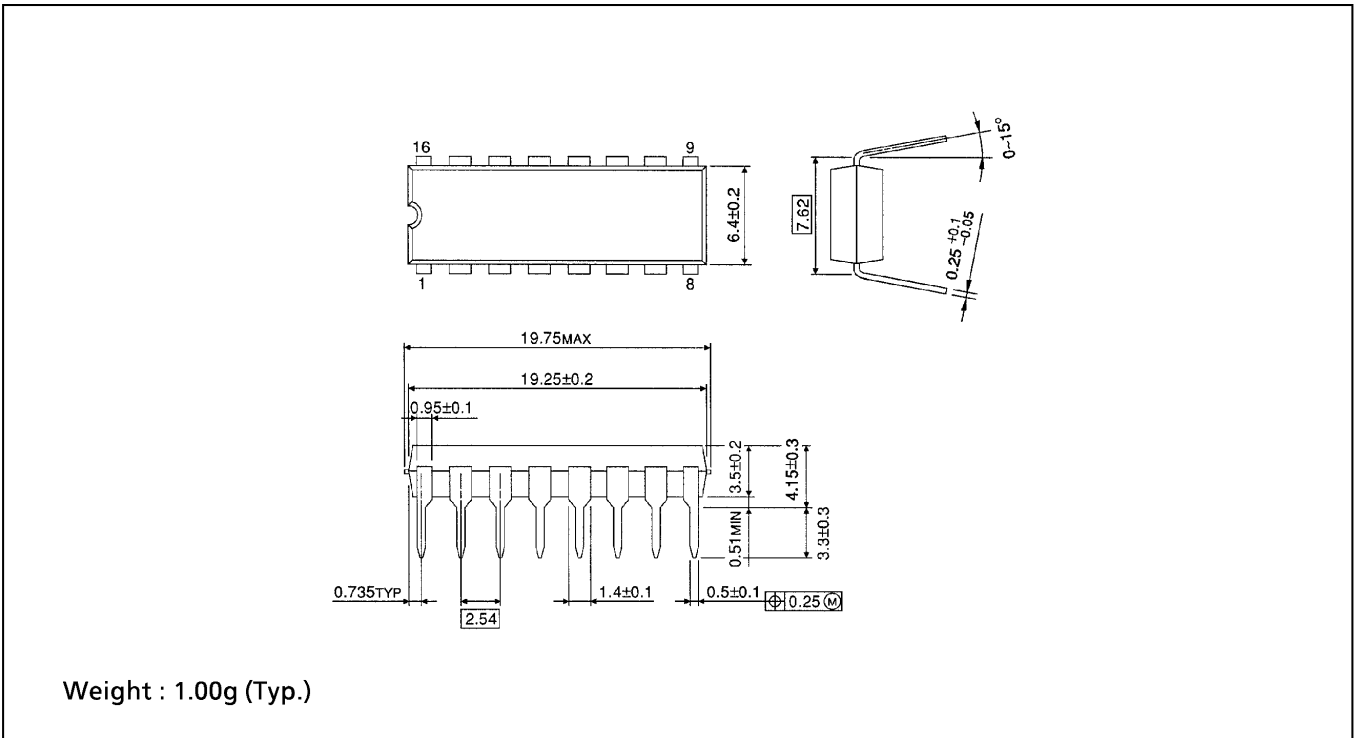
$$I_{CC}(\text{opr}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/4 \text{ (per circuit)}$$

SYSTEM DIAGRAM



DIP 16PIN OUTLINE DRAWING (DIP16-P-300-2.54A)

Unit in mm



SOP 16PIN (200mil BODY) OUTLINE DRAWING (SOP16-P-300-1.27)

Unit in mm

